# **Monolithic Amplifier**

0.5-2.5 GHz

#### **Product Features**

- 3V & 5V operation
- · no external biasing circuit required
- internal DC blocking at RF input and output
- high directivity, 20 dB typ.
- wide bandwidth, 0.5 to 2.5 GHz
- low noise figure, 5.5 dB typ.
- output power, up to +18.2 dBm typ.
- low cost



CASE STYLE: XX211-1 PRICE: \$2.50 ea. QTY. (20)

#### +RoHS Compliant

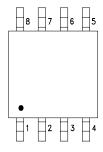
The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

## **Typical Applications**

- buffer amplifier
- cellular
- PCN

#### **General Description**

VNA-25+ is a wideband amplifier offering high dynamic range. It has repeatable performance from lot to lot. It is enclosed in an 8-lead SOIC package. VNA-25+ is fabricated using GaAs MESFET technology. Expected MTBF at 85°C case temperature is 40,000 years at 2.8V, 2,000 at 5V.



#### Pin Description

·						
Function	Pin Number	Description				
RF IN	3	RF input pin.				
RF OUT	6	RF output pin.				
DC	1	Bias pin				
GND	2,4,5,7,8	Connections to ground. Use via holes as shown in "Suggested Layout for PCB Design" to reduce ground path inductance for best performance.				



## **Electrical Specifications at 25°C**

Parameter			Тур.		Max.	Units
Frequency Range		0.5			2.5	GHz
at DC Volts		5.0	5.0	2.8	5.0	V
Gain	f=0.5 GHz		15.5	14.5		
	f=1.0 GHz		18.0	16.7		
	f=1.5 GHz	10	18.6	17.4		dB
	f=2.0 GHz f=2.5 GHz	16	17.8 16	17 15.5		
Input Return Loss	f=0.75 to 2.5 GHz		14	14		
						dB
Output Return Loss	f=0.75 to 2.5 GHz		12.5	12.5		
						dB
Output Power @ 1 dB compression	f=0.5 to 2.5 GHz		18.2	12		
						dBm
Output IP3	f=0.5 to 2.5 GHz		29	24		dBm
Noise Figure	f=0.5 to 2.5 GHz		5.5	5.5		dB
Directivity (Isolation-Gain)	f=0.5 to 2.5 GHz		18-24	16-25		dB
DC Current			85	80	105	mA
Thermal Resistance, junction-to-case <sup>1</sup>				125		°C/W

## **Absolute Maximum Ratings**

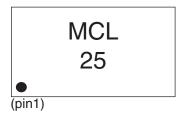
Parameter	Ratings			
Operating Temperature	-40°C to 85°C			
Storage Temperature	-55°C to 150°C			
DC Voltage	+7V, -1.0V reverse			
Power Dissipation	1000mW			
Input Power	10dBm			

Note: Permanent damage may occur if any of these limits are exceeded. These ratings are not intended for continuous normal operation.

¹Case is defined as ground leads.



## **Product Marking**



#### **Additional Detailed Technical Information**

Additional information is available on our web site. To access this information enter the model number on our web site home page.

Performance data, graphs, s-parameter data set (.zip file)

Case Style: XX211-1

VNA-25+: Plastic molded, 8-lead SOIC, lead finish: Tin Plate

Tape & Reel: F16

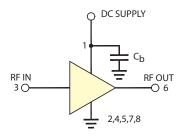
7" reels with 20, 50, 100, 200, 500 or 1K devices. 13" reel with 2.5K devices.

Suggested Layout for PCB Design: PL-077

**Evaluation Board: TB-01** 

**Environmental Ratings: ENV08T1** 

## **Recommended Application Circuit**



 $$C_b\!\!=\!100pF$  to 10~nF Test Board includes case, connectors, and components (in bold) soldered to PCB

For detailed performance specs & shopping online see web site

## **ESD Rating**

Human Body Model (HBM): Class 1A (250 v to < 500 v) in accordance with ANSI/ESD STM 5.1 - 2001

Charged Device Model (CDM): Class III (500 v to 1000v) in accordance with JESD22-C101A

#### **MSL Rating**

Moisture Sensitivity: MSL1 in accordance with IPC/JEDECJ-STD-020C

No.	Test Required	Condition	Standard	Quantity
1	Visual Inspection	Low Power Microscope Magnification 40x	MIP-IN-0003 (MCT spec)	10 units
2	Electrical Test	Room Temperature	SCD (MCL spec)	10 units
3	SAM Analysis	Less than 10% growth in term of delamination	J-Std-020C (Jedec Standard)	10 units
4	Moisture Sensitivity Level 1	Bake at 125°C for 24 hours Soak at 85°C/85%RH for 168 hours Reflow 3 cycles at 260°C peak	J-Std-020C (Jedec Standard)	10 units

#### **MSL Test Flow Chart**

